

Notice of References Cited		Application/Control No. 10/849,589	Applicant(s)/Patent Under Reexamination SAXLER, ADAM WILLIAM	
		Examiner John C. Ingham	Art Unit 2814	Page 1 of 1

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	M	US-			

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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.